

## GMBT2411 NPN SILICON PLANAR MEDIUM POWER TRANSISTOR

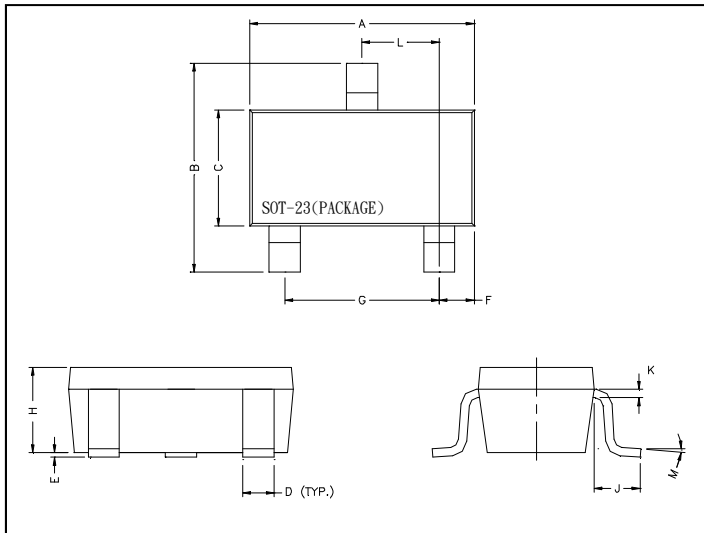
### Description

The GMBT2411 is designed for medium power amplifier applications.

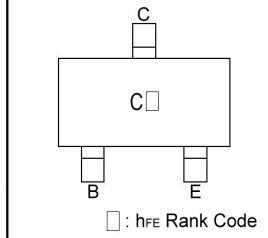
### Features

- $I_{CMax.}=500mA$
- Low  $V_{CE(sat)}$ . Optimal for low voltage operation.
- Complementary to GMBT1036

### Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

### Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Ratings	Unit
Junction Temperature	$T_j$	+150	$^\circ C$
Storage Temperature	$T_{stg}$	-55~+150	$^\circ C$
Collector to Base Voltage	$V_{CB0}$	40	V
Collector to Emitter Voltage	$V_{CE0}$	32	V
Emitter to Base Voltage	$V_{EB0}$	5	V
Collector Current	$I_C$	500	mA
Total Power Dissipation	$P_D$	225	mW

### Electrical Characteristics ( $T_a = 25^\circ C$ , unless otherwise stated)

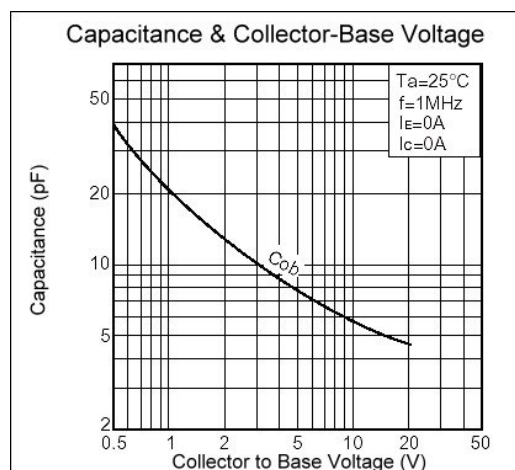
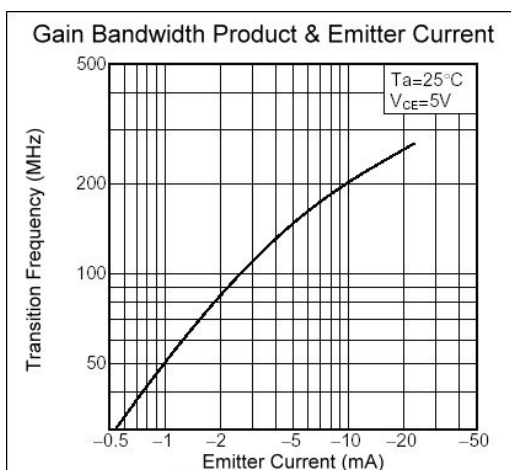
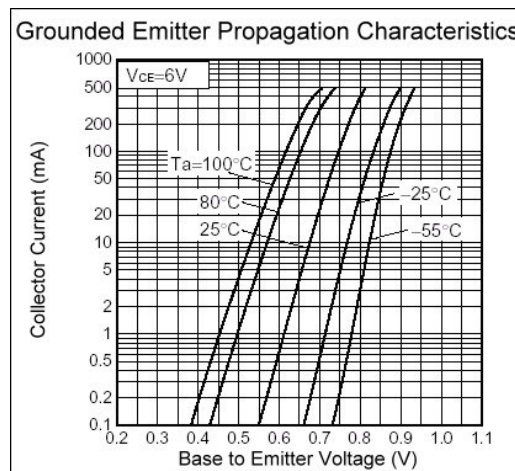
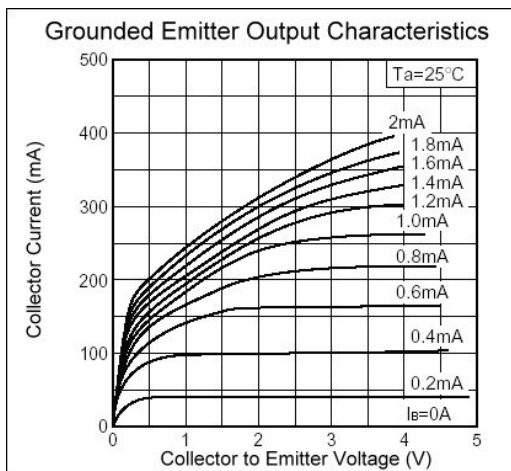
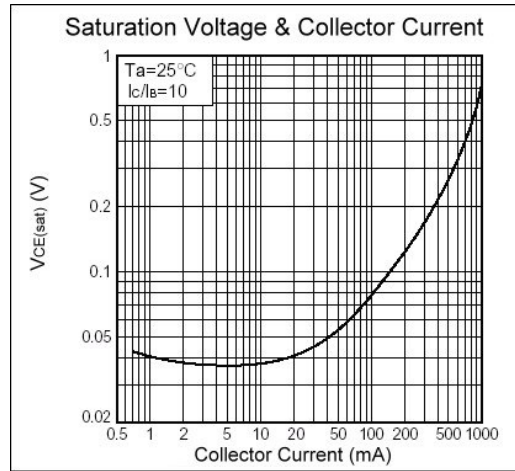
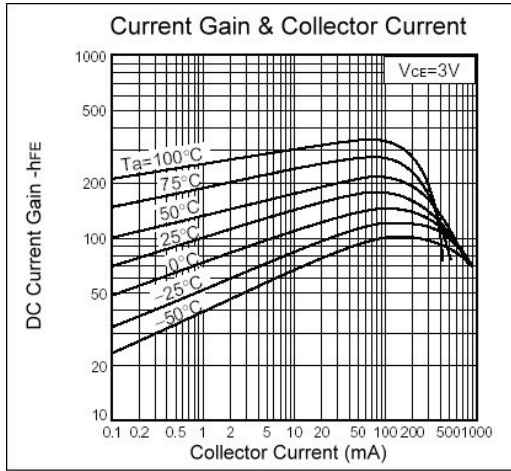
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
$V_{CB0}$	40	-	-	V	$I_C=100\mu A, I_E=0$
$V_{CE0}$	32	-	-	V	$I_C=1mA, I_B=0$
$V_{EB0}$	5	-	-	V	$I_E=100\mu A, I_C=0$
$I_{CB0}$	-	-	1	$\mu A$	$V_{CB}=20V, I_E=0$
$I_{EB0}$	-	-	1	$\mu A$	$V_{EB}=4V, I_C=0$
* $V_{CE(sat)}$	-	-	400	mV	$I_C=500mA, I_B=50mA$
*hFE	82	-	390		$V_{CE}=3V, I_C=100mA$
fT	-	250	-	MHz	$V_{CE}=5V, I_E=-20mA, f=100MHz$
Cob	-	6	-	pF	$V_{CB}=10V, I_E=0, f=1MHz$

\*Measured under pulse condition. Pulse width=300 $\mu s$ , Duty Cycle $\leq 2\%$

### Classification Of hFE

Rank	CP	CQ	CR
Range	82 - 180	120 - 270	180 - 390

## Characteristics Curve



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